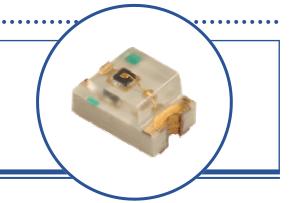
Infrared Light Emitting Diode in Miniature SMD Package





- Flat Lens
- High Power
- 0805 Package Size
- 880nm Wavelength

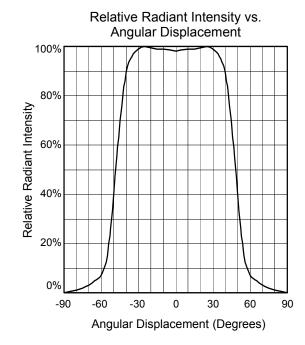


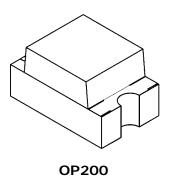
The OP200 is a GaAlAs infrared LEDs mounted in a miniature SMT package. The device incorporates a flat molded lens which enables a wide beam angle and provides an even emission pattern. This device is packaged in a 0805 size chip carrier that is compatible with most automated mounting equipment. The OP200 is mechanically and spectrally matched to the OP520 series phototransistors.

Applications

- Non-Contact Position Sensing
- Datum detection

- Machine automation
- Optical encoders









SMD Infrared LED **OP200**



Absolute Maximum Ratings T_A = 25° C unless otherwise noted

Storage Temperature Range	-40° C to +85° C
Operating Temperature Range	-25° C to +85° C
Lead Soldering Temperature	260° C ⁽¹⁾
Reverse Voltage	30 V
Continuous Forward Current	50 mA
Power Dissipation	130 mW ⁽²⁾

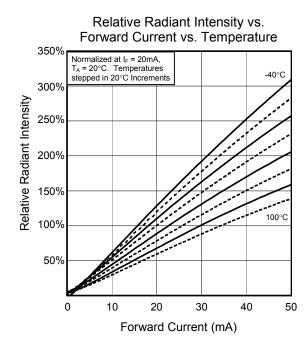
Notes:

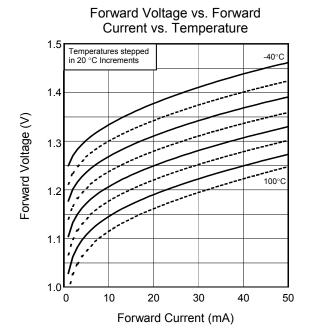
- Solder time less than 5 seconds at temperature extreme.
- De-rate linearly at 2.17 mW/° C above 25° C.

Electrical Characteristics (T_A = 25°C unless otherwise noted)

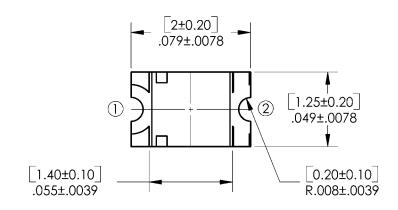
SYMBOL	PARAMETER	MIN	TYP	MAX	UNITS	CONDITIONS
E _{e(APT)}	Apertured Radiant Incidence	0.2			mW/cm ²	I _F = 20mA ⁽³⁾
V _F	Forward Voltage			1.5	V	I _F = 20mA
I _R	Reverse Current			100	μΑ	V _R = 2.0V
λ_{P}	Peak Emission Wavelength		890		nm	I _F = 10mA
ӨнР	Emission Angle at Half Power Points		100		Deg.	I _F = 20mA
t _r , t _f	Rise and Fall Time			500	ns	$I_{F(PEAK)}$ = 100mA, PW = 10 μ s, 10% D.C.

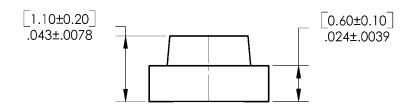
 $E_{e(APT)}$ is a measurement of the apertured radiant incidence upon a sensing area 0.081" (2.06mm) in diameter, perpendicular to and centered on the mechanical axis of the lens, and 0.590" (14.99mm) from the measurement surface. $E_{e(APT)}$ is not necessarily uniform within the measured area.

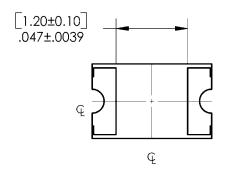












PIN	FUNCTION	
1	Anode	
2	Cathode	

DIMENSIONS ARE IN INCHES AND [MILLIMETERS].